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December 2008

FDG332PZ

P-Channel PowerTrench® MOSFET

-20V, -2.6A, 97m Ω

Features

- Max $r_{DS(on)}$ = 95m Ω at V_{GS} = -4.5V, I_D = -2.6A
- Max $r_{DS(on)}$ = 115m Ω at V_{GS} = -2.5V, I_D = -2.2A
- Max $r_{DS(on)}$ = 160m Ω at V_{GS} = -1.8V, I_D = -1.9A
- Max $r_{DS(on)} = 330 \text{m}\Omega$ at $V_{GS} = -1.5 \text{V}$, $I_D = -1.0 \text{A}$
- Very low level gate drive requirements allowing operation in 1.5V circuits
- Very small package outline SC70-6
- RoHS Compliant

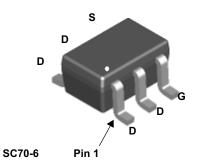


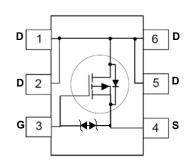
General Description

This P-Channel MOSFET uses Fairchild's advanced low voltage PowerTrench[®] process. It has been optimized for battery power management applications.

Applications

- Battery management
- Load switch





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		-20	V
V_{GS}	Gate to Source Voltage		±8	V
	Drain Current -Continuous		-2.6	^
ID	-Pulsed		-9	A
Ь	Power Dissipation (Not	te 1a)	0.75	W
P _D	Power Dissipation (Not	te 1b)	0.48	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

				_
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1a)	170	°C/W
Rain	Thermal Resistance, Junction to Ambient Single operation	(Note 1b)	260	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.2P	FDG332PZ	SC70-6	7"	8 mm	3000 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = -250μA, referenced to 25°C		-13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16V, \ V_{GS} = 0V$			-1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8V, V_{DS} = 0V$			±10	μΑ

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.4	-0.7	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = -250μA, referenced to 25°C		2.5		mV/°C
	$V_{GS} = -4.5V, I_D = -2.6A$		73	95		
	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -2.2A$		90	115	
r _{DS(on)}		$V_{GS} = -1.8V, I_D = -1.9A$		117	160	mΩ
		$V_{GS} = -1.5V, I_D = -1.0A$		147	330	
		$V_{GS} = -4.5V$, $I_D = -2.6A$, $T_J = 125$ °C		100	133	
9 _{FS}	Forward Transconductance	V _{DD} = -5V, I _D = -2.6A		9		S

Dynamic Characteristics

C _{iss}	Input Capacitance		420	560	pF
C _{oss}	Output Capacitance	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHZ$	85	115	pF
C _{rss}	Reverse Transfer Capacitance		75	115	pF

Switching Characteristics

	•				
t _{d(on)}	Turn-On Delay Time		5.2	10	ns
t _r	Rise Time	$V_{DD} = -10V, I_{D} = -2.6A,$	4.8	10	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = -4.5V, R_{GEN} = 6Ω	59	95	ns
t _f	Fall Time		28	45	ns
Q_g	Total Gate Charge		7.6	10.8	nC
Q _{gs}	Gate to Source Charge	$V_{GS} = -4.5V, V_{DD} = -10V, I_{D} = -2.6A$	0.9		nC
Q_{gd}	Gate to Drain "Miller" Charge		1.9		nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current				-0.6	Α
V _{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = -0.6A$ (Note 2)		-0.7	-1.2	V
t _{rr}	Reverse Recovery Time	-I _F = 2.6A, di/dt = 100A/μs		28	45	ns
Q _{rr}	Reverse Recovery Charge			8	13	nC

Notes:

^{1.} $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 170°C/W when mounted on a 1 in² pad of 2 oz copper.



 b. 260°C/W when mounted on a minimum pad of 2 oz copper.

^{2.} Pulse Test: Pulse Width < $300\mu s$, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

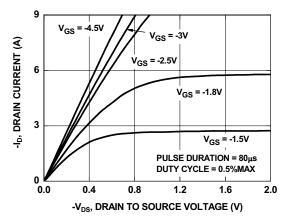


Figure 1. On-Region Characteristics

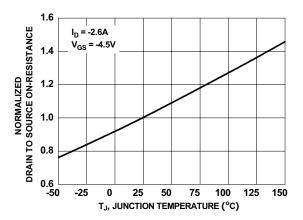


Figure 3. Normalized On-Resistance vs Junction Temperature

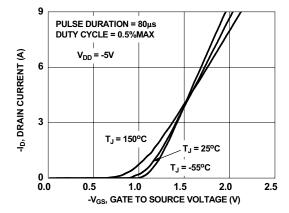


Figure 5. Transfer Characteristics

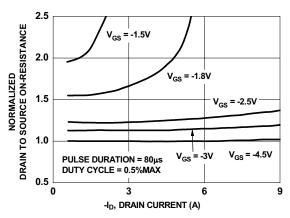


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

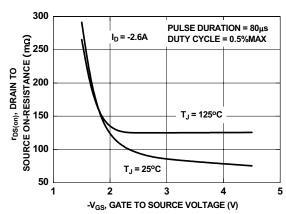


Figure 4. On-Resistance vs Gate to Source Voltage

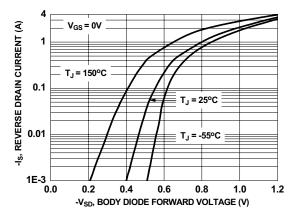


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

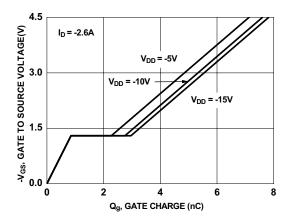


Figure 7. Gate Charge Characteristics

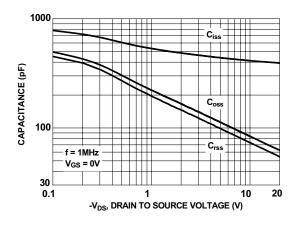


Figure 8. Capacitance vs Drain to Source Voltage

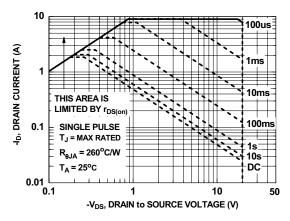


Figure 9. Forward Bias Safe Operating Area

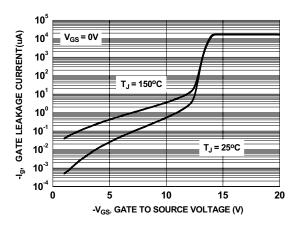


Figure 10. Gate Leakage Current vs Gate to Source Voltage

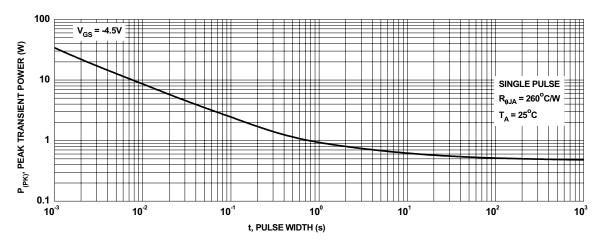


Figure 11. Transient Thermal Response Curve

Typical Characteristics T_J = 25°C unless otherwise noted

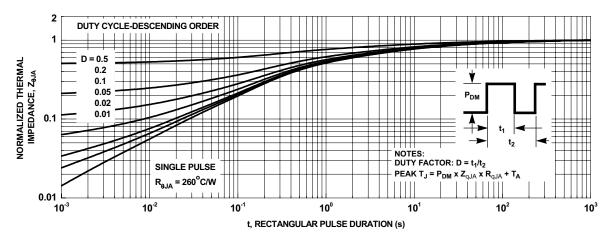


Figure 12. Transient Thermal Response Curve





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